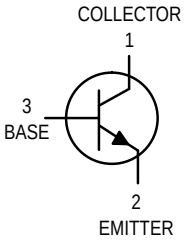
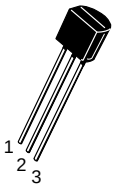
VHF Transistor

NPN Silicon

BF959





CASE 29–04, STYLE 21
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	20	Vdc
Collector–Base Voltage	V_{CBO}	30	Vdc
Emitter–Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	100	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 5.0 mAdc, V_{CE} = 10 Vdc) (I_C = 20 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 35 40	 — —	 — —	—
Collector–Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 2.0 mAdc)	$V_{CE(sat)}$	—	—	1.0	Vdc
Base–Emitter Saturation Voltage (I_C = 30 mAdc, I_B = 2.0 mAdc)	$V_{BE(sat)}$	—	—	1.0	Vdc
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 100 MHz) (I_C = 30 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	 700 600	 — —	 — —	MHz
Common Emitter Feedback Capacitance (V_{CB} = 10 Vdc, P_f = 0, f = 10 MHz)	C_{re}	—	0.65	—	pF
Noise Figure (I_C = 4.0 mA, V_{CE} = 10 V, R_S = 50 Ω, f = 200 MHz)	N_f	—	3.0	—	dB

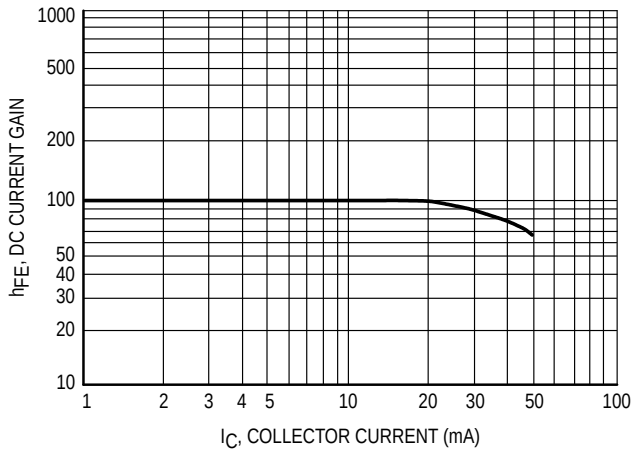


Figure 1. h_{FE} at 10 V

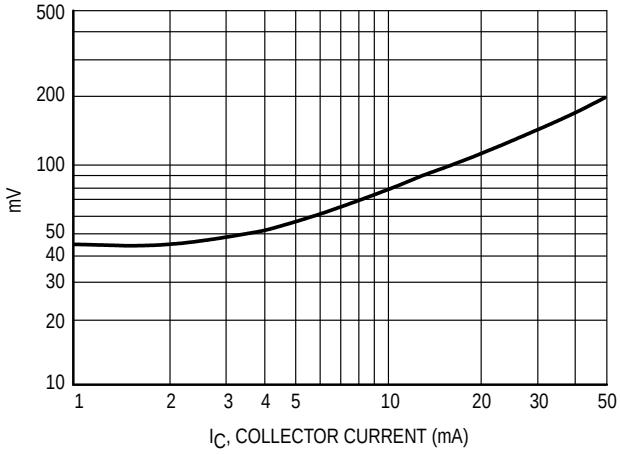


Figure 2. $V_{CE(sat)}$ at I_C/I_B = 10

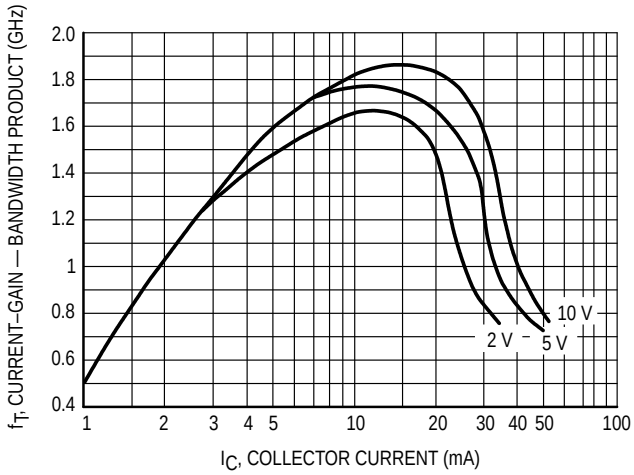


Figure 3. Current–Gain — Bandwidth Product

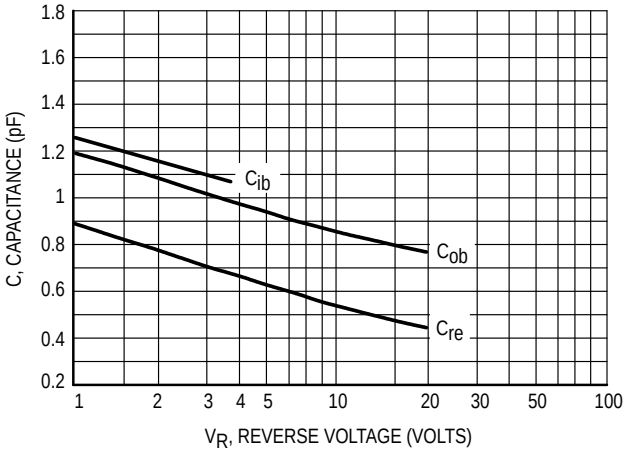


Figure 4. Capacitances

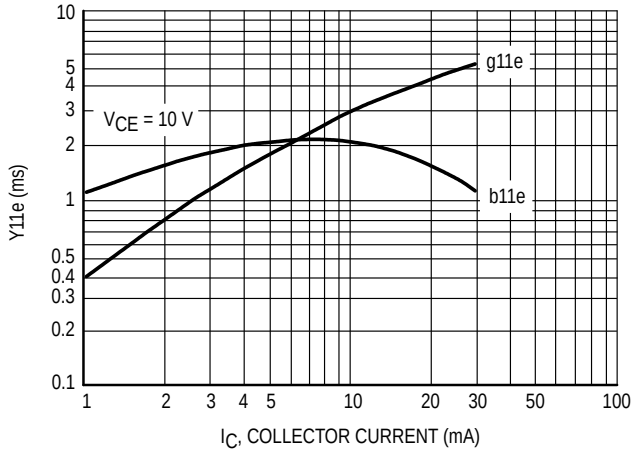


Figure 5. Input Impedance at 30 MHz

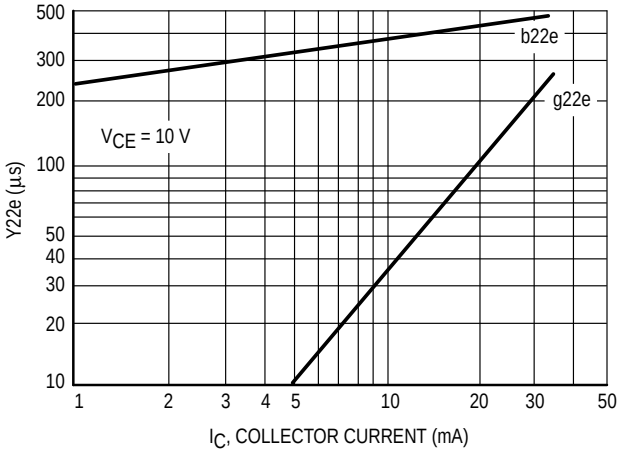
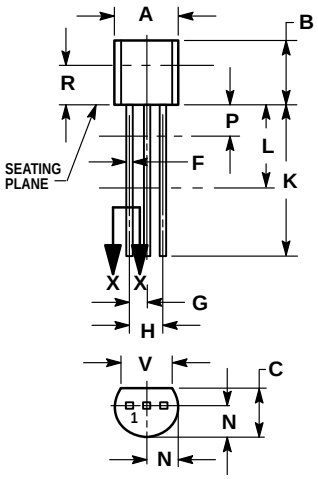
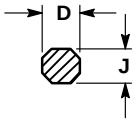


Figure 6. Output Impedance at 30 MHz

PACKAGE DIMENSIONS





SECTION X–X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 21:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

CASE 029–04
(TO–226AA)
ISSUE AD

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